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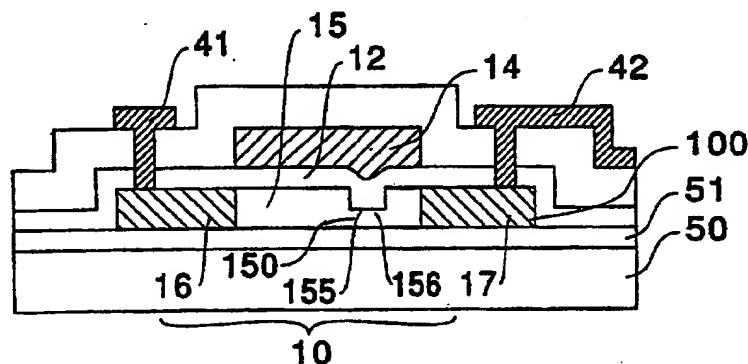
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(54) Abstract Title
Thin film transistors

(57) The transistor comprises a channel region 15 having a recess 155 such that when a polycrystalline film 100 is annealed, the degree of crystallisation in the region of the recess is reduced, thereby concentrating defects at the recess, which defects act as a recombination centre 150. Instead of a recess, a hump or depression may be formed in the channel region. The recombination centre prevents the bipolar transistor type behaviour of a conventional thin film transistor.

Fig. 2



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